

ROITHNER LASERTECHNIK

A-1040 WIEN, FLEISCHMANNGASSE 9

TEL: +43 -1- 586 52 43 FAX: +43 -1- 586 41 43

e-mail: office@roithner-laser.com http://www.roithner-laser.com

RLT808150GO TECHNICAL DATA

High Power Infrared Laserdiode

Emitting Dimensions: **100 x 1 μm**

Lasing wavelength: **808 nm typ.**

Max. optical power: **150 mW**

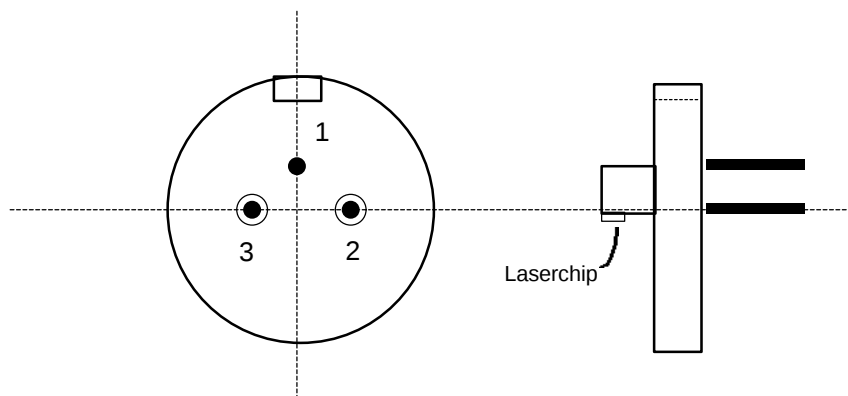
Package: **9 mm open package**



NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:

- 1: laserdiode anode
- 2: N.C.
- 3: laserdiode cathode



Absolute Maximum Ratings (T_c=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	200	mW
LD Reverse Voltage	V _{R(LD)}	2	V
Operating Case Temperature	T _C	-20 .. +50	°C
Storage Temperature	T _{STG}	-55 .. +80	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	cw		150		mW
Operation Current	I _{op}	P _o = 150 mW		0.4		A
Operation Voltage	V _{op}	P _o = 150 mW		2.4		V
Lasing Wavelength	λ_p	P _o = 150 mW	805	808	811	nm
Beam Divergence	θ	P _o = 150 mW		10x30		°